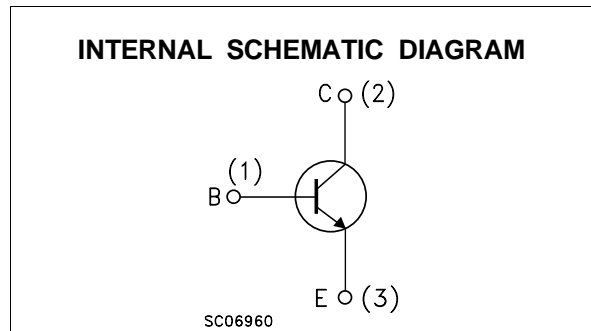
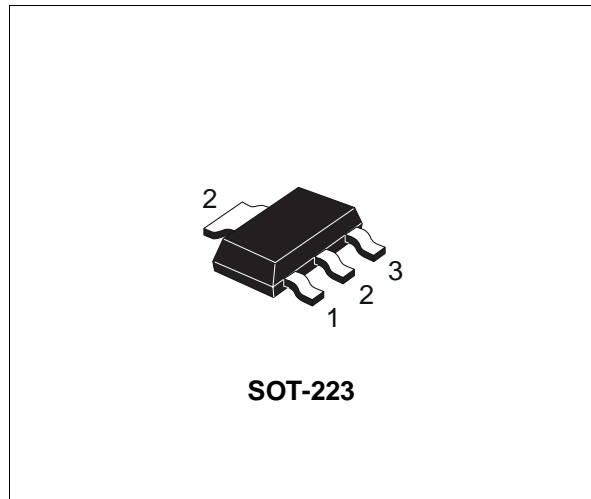


**MEDIUM POWER AMPLIFIER**

**ADVANCE DATA**

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- GENERAL PURPOSE MAINLY INTENDED FOR USE IN MEDIUM POWER INDUSTRIAL APPLICATION AND FOR AUDIO AMPLIFIER OUTPUT STAGE
- PNP COMPLEMENT IS STZTA92



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	300	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	300	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	6	V
$I_C$	Collector Current	0.1	A
$I_{CM}$	Collector Peak Current	0.3	A
$P_{tot}$	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	2	W
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

## STZTA42

### THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	62.5	$^{\circ}\text{C}/\text{W}$
$R_{thj-tab}$	Thermal Resistance Junction-Collector Tab	Max	8	$^{\circ}\text{C}/\text{W}$

• Mounted on a ceramic substrate area = 30 x 35 x 0.7 mm

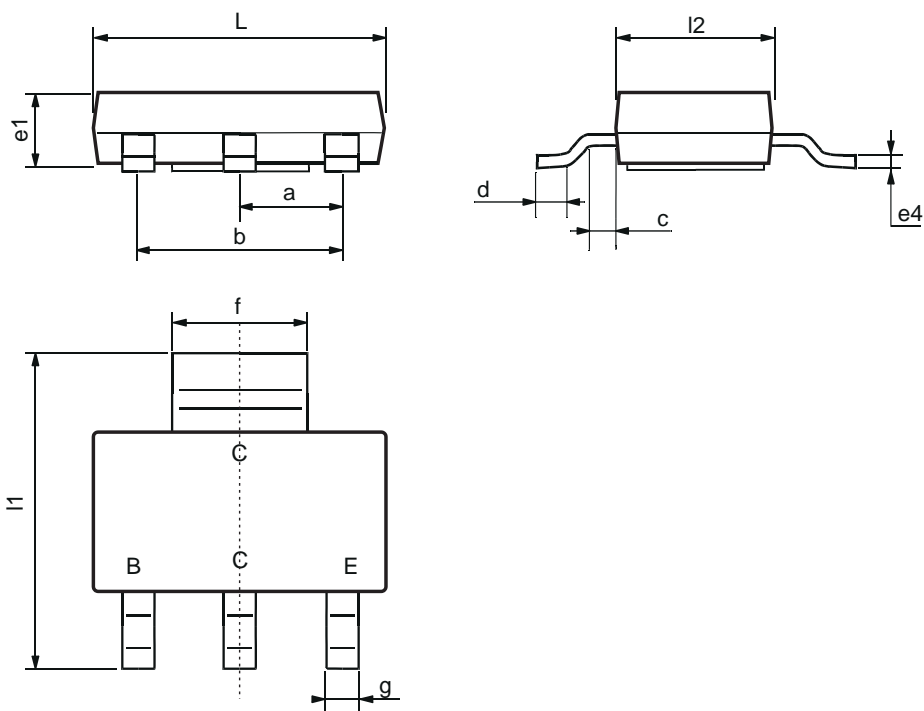
### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = 200\text{ V}$			100	nA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_E = 0$ )	$I_C = 100\ \mu\text{A}$	300			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = 1\text{ mA}$	300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_C = 0$ )	$I_E = 100\ \mu\text{A}$	6			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 20\text{ mA}$ $I_B = 2\text{ mA}$			0.5	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 20\text{ mA}$ $I_B = 2\text{ mA}$			0.9	V
$h_{FE}^*$	DC Current Gain	$I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 30\text{ mA}$ $V_{CE} = 10\text{ V}$	25 40 40			
$f_T$	Transition Frequency	$I_C = 10\text{ mA}$ $V_{CE} = 20\text{ V}$ $f = 50\text{ MHz}$	50			MHz
$C_{CEO}$	Collector Emitter Capacitance	$V_{CE} = 20\text{ V}$ $f = 1\text{ MHz}$	50			pF

\* Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle  $\leq 1.5\%$

## SOT223 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



P008B

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